



12V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	15mΩ @ $V_{GS} = -4.5V$	-8.5A
-12V	20mΩ @ V _{GS} = -3.7V	-7.3A
	$25m\Omega @ V_{GS} = -3.3V$	-6.6A
	30mΩ @ V _{GS} = -2.5V	-6.0A
	40mΩ @ V _{GS} = -1.8V	-5.2A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

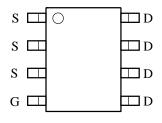
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

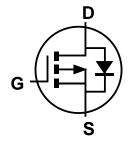
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)







Top View Internal Schematic



Equivalent Circuit

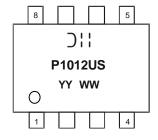
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMP1012USS-13	SO-8	2,500/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



⊃¦¦ = Manufacturer's Marking P1012US = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 18 = 2018) WW = Week (01 to 53)

August 2018



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-12	V		
Gate-Source Voltage	V_{GSS}	±8	V		
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	-8.5 -6.8	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-40	Α		
Maximum Continuous Body Diode Forward Current (Note (Is	-2	Α		
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	-40	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	-21	Α
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	22	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	Steady State	$T_A = +25^{\circ}C$	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)			$R_{ heta JA}$	99	°C/W
Total Power Dissipation (Note 6) Steady State		T _A = +25°C	P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 6) Steady state			$R_{ heta JA}$	77	°C/W
Thermal Resistance, Junction to Case (Note 6)			$R_{\theta JC}$	13	-C/VV
Operating and Storage Temperature Range			$T_{J_i} T_{STG}$	-55 to +150	°C

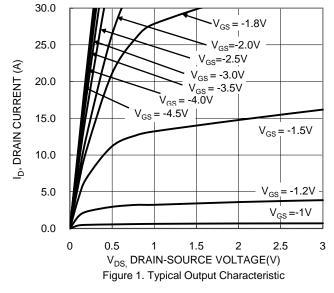
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	-0.4	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			9	15	mΩ	$V_{GS} = -4.5V, I_D = -9A$	
		_	10	20		$V_{GS} = -3.7V, I_D = -7A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		11	25		$V_{GS} = -3.3V, I_D = -7A$	
			13	30		$V_{GS} = -2.5V, I_D = -6A$	
			18	40		$V_{GS} = -1.8V, I_D = -4A$	
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1344	_		101/1/	
Output Capacitance	Coss	_	342	_	pF	VDS = -10V, VGS = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	297	_			
Gate Resistance	Rg	_	15	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	19.5	_			
Total Gate Charge (V _{GS} = -8V)	Qg	_	31	_	nC	V _{DS} = -6V. I _D = -10A	
Gate-Source Charge	Q _{gs}	_	2.1	_	IIC	VDS = -6V, ID = -10A	
Gate-Drain Charge	Q_{gd}	_	7.9	_			
Turn-On Delay Time	t _{D(ON)}	_	6.0	_			
Turn-On Rise Time	t _R	_	32	_		$V_{DS} = -6V, V_{GS} = -4.5V,$ $R_g = 1\Omega, I_D = -8A$	
Turn-Off Delay Time	t _{D(OFF)}	_	71	_	ns		
Turn-Off Fall Time	t _F	_	85	_			
Reverse Recovery Time	t _{RR}	_	46	_	ns	1 404 41/44 5004/:	
Reverse Recovery Charge	Q _{RR}	_	44	_	nC	$I_F = -12A$, di/dt = 500A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Device mounted on FR-4 substrate PC board, 202 copper, with minimum recommended parts.
 Les mounted on FR-4 substrate PC board, 202 copper, with 1inch square copper plate.
 I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





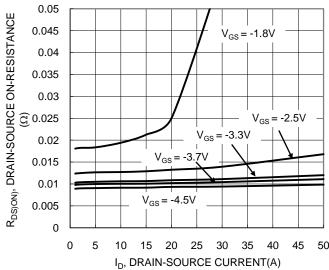


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

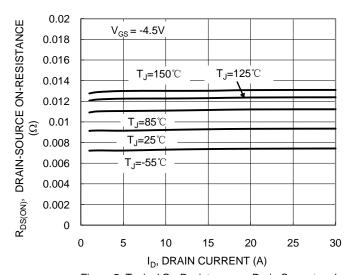
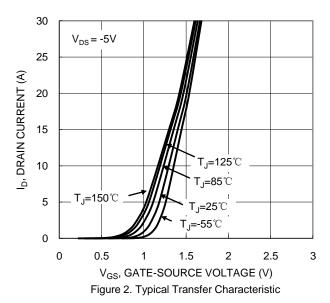


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



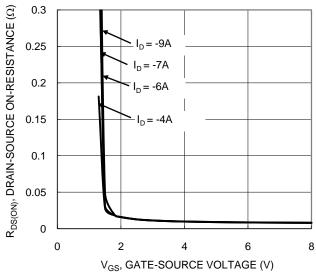


Figure 4. Typical Transfer Characteristic

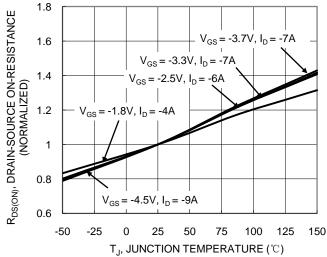


Figure 6. On-Resistance Variation with Junction Temperature



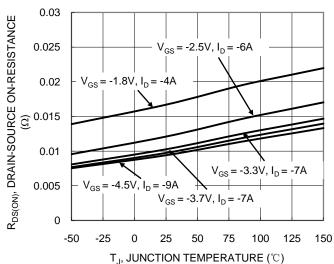
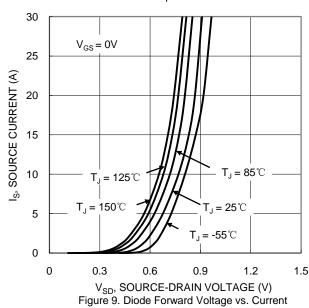


Figure 7. On-Resistance Variation with Junction Temperature



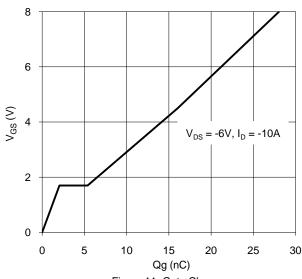


Figure 11. Gate Charge

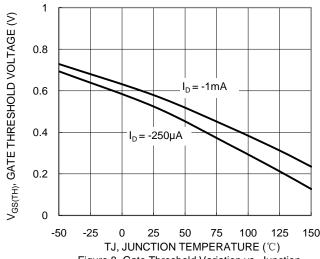
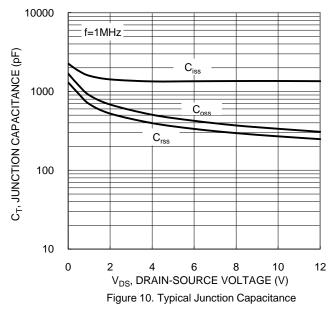
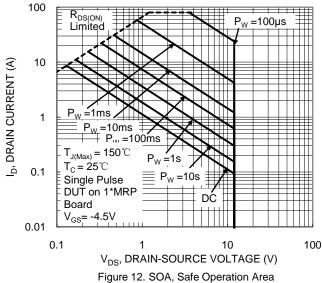


Figure 8. Gate Threshold Variation vs. Junction Temperature







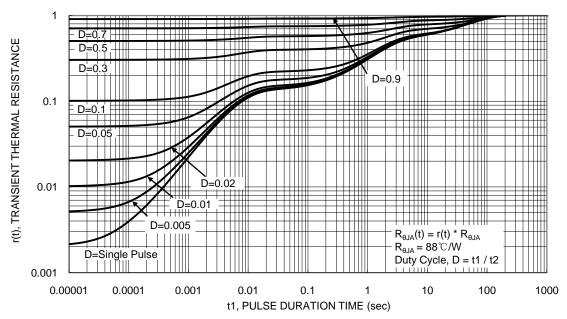
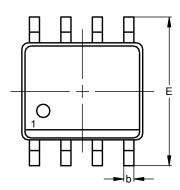


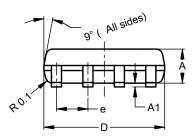
Figure 13. Transient Thermal Resistance

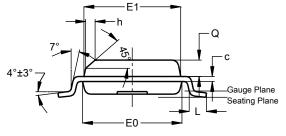


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.





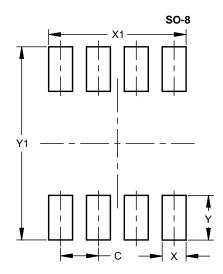


SO-8

SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Ε	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0 3.85		3.95	3.90		
e 1.27					
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)				
С	1.27				
Х	0.802				
X1	4.612				
Υ	1.505				
Y1	6.50				



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